Yixin

Advanced Power MOSFET

IRFS640A

FEATURES

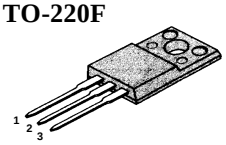
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10 μA (Max.) @ V_{DS} = 200V
- Lower $R_{DS(ON)}$: 0.144 Ω (Typ.)

BV_{DSS} = 200 V

$R_{DS(on)}$ = 0.18 Ω

I_D = 9.8 A

TO-220F



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	200	V
I_D	Continuous Drain Current (T_C=25 °C)	9.8	A
	Continuous Drain Current (T_C=100 °C)	6.2	
I_{DM}	Drain Current-Pulsed ①	72	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ②	256	mJ
I_{AR}	Avalanche Current ①	9.8	A
E_{AR}	Repetitive Avalanche Energy ①	4.3	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
P_D	Total Power Dissipation (T_C=25 °C) Linear Derating Factor	43 0.35	W W/°C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8 " from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	2.89	°C/W
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	200	--	--	V	V_{GS}=0V,I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.26	--	V/°C	I_D=250 μA ***See Fig 7***
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=5V,I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=30V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-30V
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	V_{DS}=200V
		--	--	100		V_{DS}=160V,T_C=125 °C
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.18	Ω	V_{GS}=10V,I_D=4.9A ④
g_{fs}	Forward Transconductance	--	8.4	--	Ω	V_{DS}=40V,I_D=4.9A ④
C_{iss}	Input Capacitance	--	1160	1500	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz ***See Fig 5***
C_{oss}	Output Capacitance	--	210	250		
C_{rss}	Reverse Transfer Capacitance	--	94	110		
$t_{d(on)}$	Turn-On Delay Time	--	17	40	ns	V_{DD}=100V,I_D=18A, R_G=9.1 Ω ***See Fig 13*** ④ ⑤
t_r	Rise Time	--	16	40		
$t_{d(off)}$	Turn-Off Delay Time	--	48	110		
t_f	Fall Time	--	24	60		
Q_g	Total Gate Charge	--	44	58	nC	V_{DS}=160V,V_{GS}=10V, I_D=18A ***See Fig 6 & Fig 12*** ④ ⑤
Q_{gs}	Gate-Source Charge	--	10.4	--		
Q_{gd}	Gate-Drain(“Miller”) Charge	--	27.1	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	9.8	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	72		
V_{SD}	Diode Forward Voltage ④	--	--	1.5	V	T_J=25°C,I_S=9.8A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	195	--	ns	T_J=25°C,I_F=18A di_F/dt=100A/μs ④
Q_{rr}	Reverse Recovery Charge	--	1.35	--	μC	

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
② L=4mH, I_{AS}=9.8A, V_{DD}=50V, R_G=27Ω , Starting T_J=25 °C
③ I_{SD}≤18A, di/dt ≤260A/ μs, V_{DD}≤BV_{DSS} , Starting T_J=25 °C
④ Pulse Test : Pulse Width = 250 μs, Duty Cycle ≤2%
⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

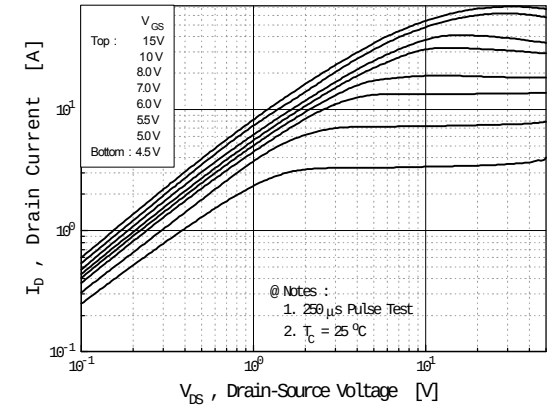


Fig 2. Transfer Characteristics

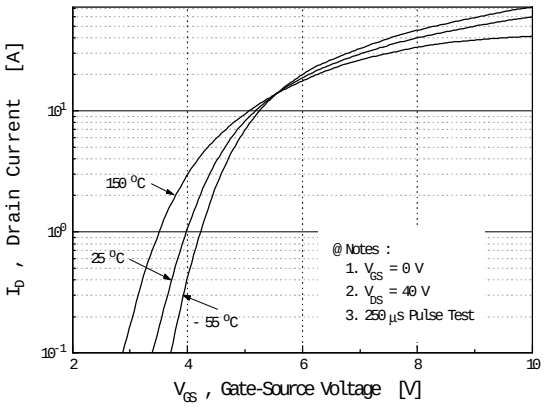


Fig 3. On-Resistance vs. Drain Current

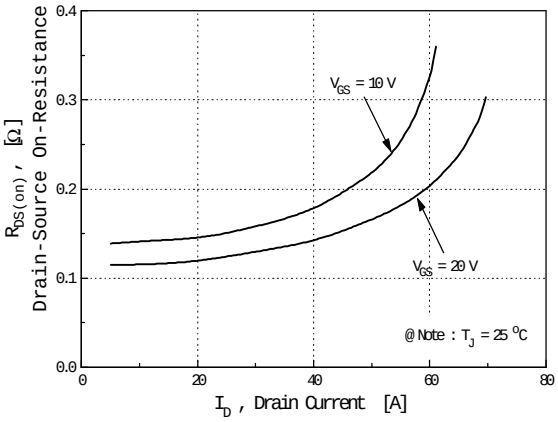


Fig 4. Source-Drain Diode Forward Voltage

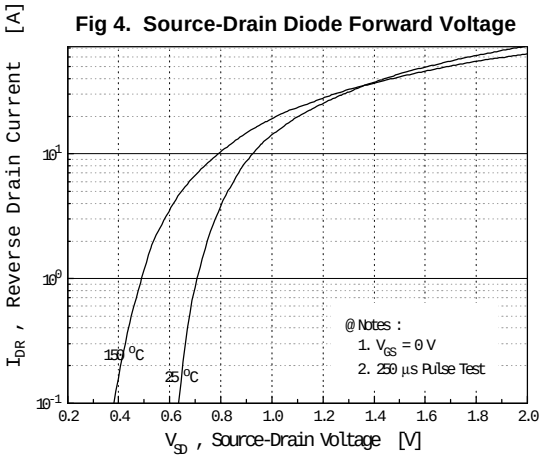


Fig 5. Capacitance vs. Drain-Source Voltage

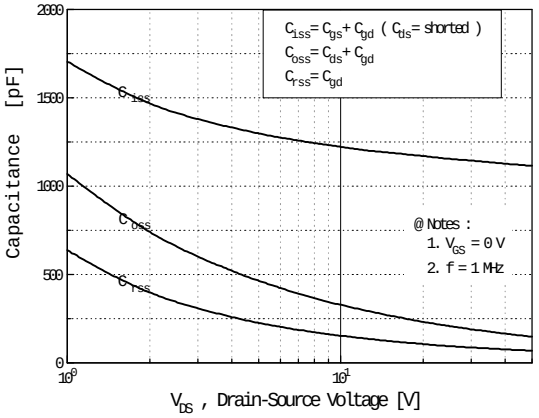


Fig 6. Gate Charge vs. Gate-Source Voltage